

FIG. 1

Figure 2. Thicknes: PC results for the medium deposition process

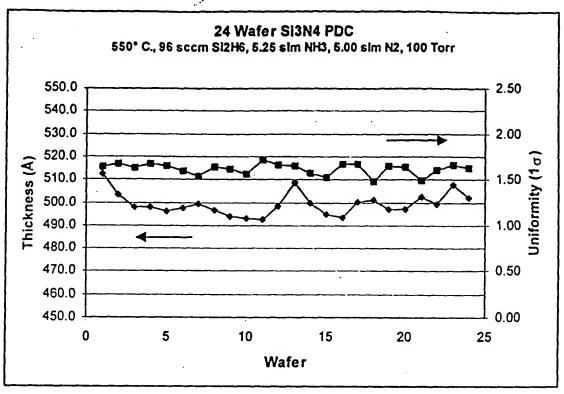


Figure 3. RI PDC results for the medium deposition rate process.

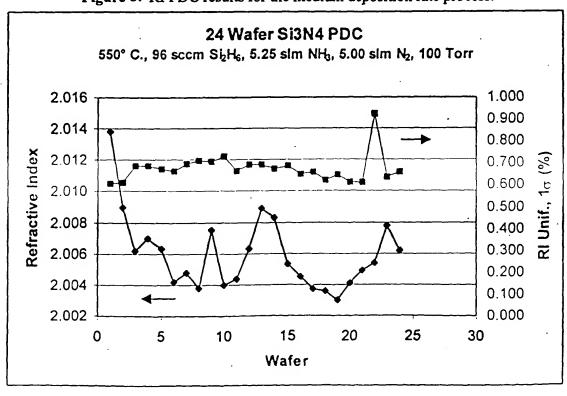
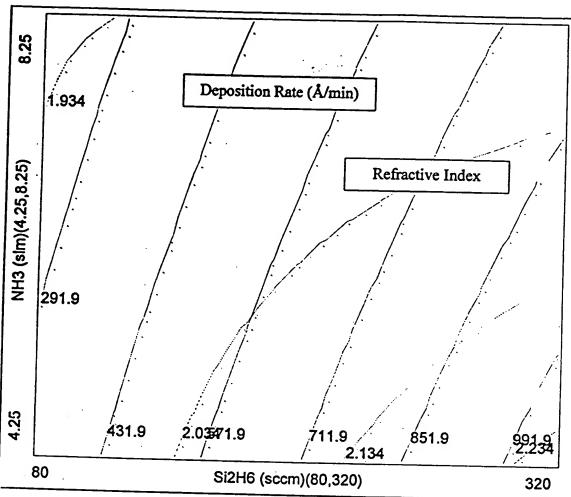
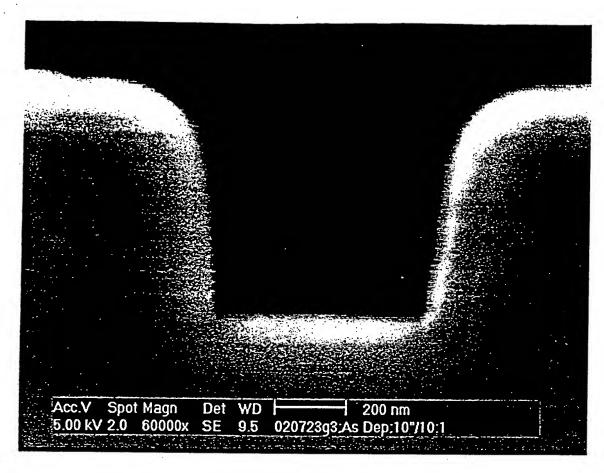


Figure 4. Effects of Si<sub>2</sub>H<sub>6</sub> and NH<sub>3</sub> on the deposition rate and RI at constant pressure, temperature and N2 flow.





550°C Si<sub>2</sub>H<sub>6</sub>-based silicon nitride (deposition rate: 500 Å/min)

FIGURE 5